EEE-2103: Electronic Devices and Circuits

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DC Load Line and Bias Point

Promble-21:

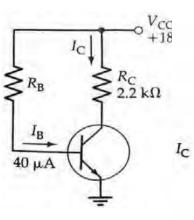
The transistor circuit in Fig. 21(a) has the collector characteristics shown in Fig. 21(b). Determine the circuit Q-point and estimate the maximum symmetrical output voltage swing. Note that V_{CC} = 18 V, R_C = 2.2 k Ω , and I_B = 40 μ A.

$$I_C = 0 \Rightarrow$$

 $V_{CE} = V_{CC} - I_C R_C = V_{CC} - 0 = 18 \text{ V}$
Point $A = (18, 0)$

$$V_{CE} = 0 \text{ V} \rightarrow 0 = V_{CC} - I_C R_C$$

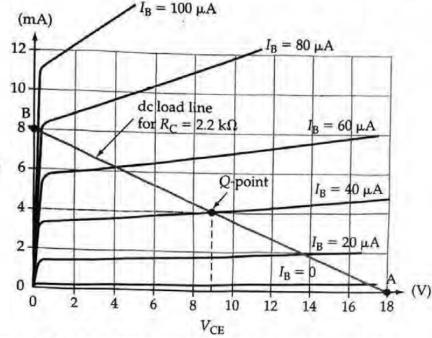
 $I_C = V_{CC} / R_C = 18/2.2 \times 10^3 \approx 8.2 \text{ mA}$
Point $B = (0, 8.2)$



Q-point is at intersection of load line and I_B = 40 μA DC bias conditions are \rightarrow

$$I_C \approx 4.1 \text{ mA} \text{ and } V_{CE} \approx 9 \text{V}$$

Max symmetrical output voltage swing, $\Delta V_{CE} \approx \pm 9 \text{ V}$



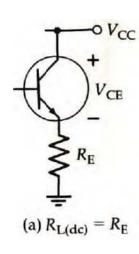
DC Load Line and Bias Point

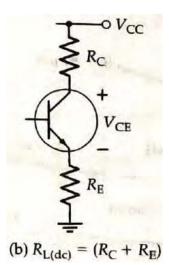
$$\begin{aligned} \text{Effect of } R_E & \boldsymbol{\rightarrow} \\ \text{DC load} &= R_E \\ V_{CE} &= V_{CC} - I_E R_E \ [I_C \approx I_E] \end{aligned}$$

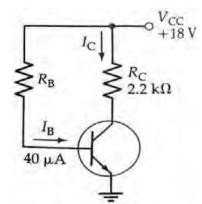
Effect of
$$R_C$$
 and $R_E \rightarrow$

$$DC \text{ load} = R_C + R_E$$

$$V_{CE} = V_{CC} - I_C(R_C + R_E)$$







For dc analysis \rightarrow

network can be isolated from ac levels replacing capacitors with open-circuit for dc, f = 0 Hz, and X_C = 1/(2 πfC) = 1/(2 π (0)C) = ∞ Ω

$$BE loop \Rightarrow \\ +V_{CC} - I_B R_B - V_{BE} = o$$

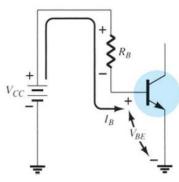
$$I_B = \frac{V_{CC} - V_{BE}}{R_B}$$

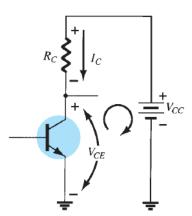
$$CE \text{ loop} \Rightarrow$$

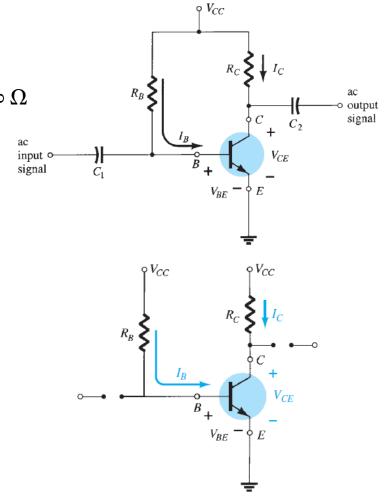
$$I_C = \beta I_B$$

$$V_{CE} + I_C R_C - V_{CC} = 0$$

$$V_{CE} = V_{CC} - I_C R_C$$







Problem-22:

Determine the following for the fixed-bias configuration of Fig. 22.

- a) I_{BO} and I_{CO} . b) V_{CEO} .
- c) V_B and V_C . d) V_{BC} .

a)
$$I_{BQ} = \frac{V_{CC} - V_{BE}}{R_B} = \frac{12 - 0.7}{240 \times 10^3} = 47.08 \,\mu\text{A}$$

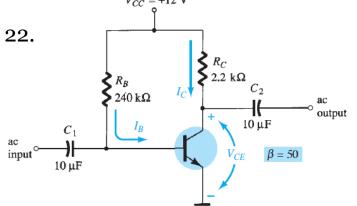
 $I_{CO} = \beta I_{BO} = (50)(47.08 \times 10^{-6}) = 2.35 \,\text{mA}$

b)
$$V_{CEQ} = V_{CC} - I_C R_C = 12 \text{ V} - (2.35 \times 10^{-3})(2.2 \times 10^3) = 6.83 \text{ V}$$

c)
$$V_B = V_{BE} = 0.7 \text{ V}$$

 $V_C = V_{CE} = 6.83 \text{ V}$

d)
$$V_{BC} = V_B - V_C = 0.7 - 6.83 = -6.13 \text{ V}$$



Transistor saturation:

saturation = levels have reached their maximum values.

transistor saturation region =

current is maximum for particular design.

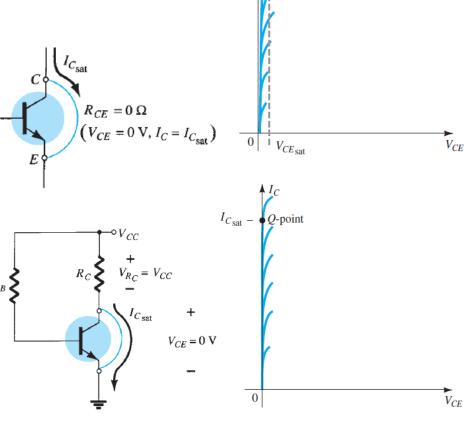
characteristic curves join.

$$V_{CE} \le V_{CEsat} \approx \text{o V}$$

 $R_{CE} = V_{CE}/I_C = \text{o}/I_{Csat} = \text{o }\Omega$

Saturation conditions are normally avoided \rightarrow *BC* junction is no longer reverse-biased output amplified signal will be distorted.

Set
$$V_{CE}$$
 = 0 V.
$$I_{Csat} = V_{CC}/R_C$$
 Keep $I_C < I_{Csat}$ if we expect linear amplification.



Load line analysis:

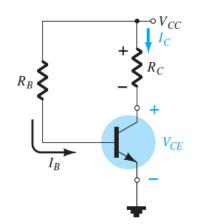
Output equation \rightarrow

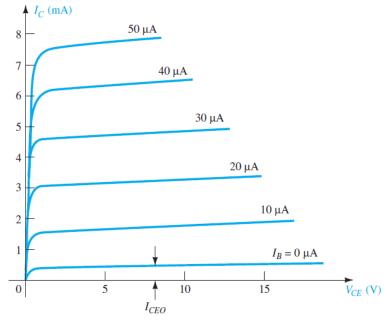
$$V_{CEQ} = V_{CC} - I_C R_C$$

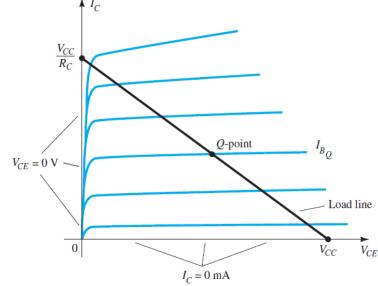
$$I_C = o \text{ mA} \rightarrow V_{CE} = V_{CC} - (o)R_C = V_{CC}$$

$$V_{CE} = o V \rightarrow o = V_{CC} - I_C R_C$$

 $I_C = V_{CC}/R_C$



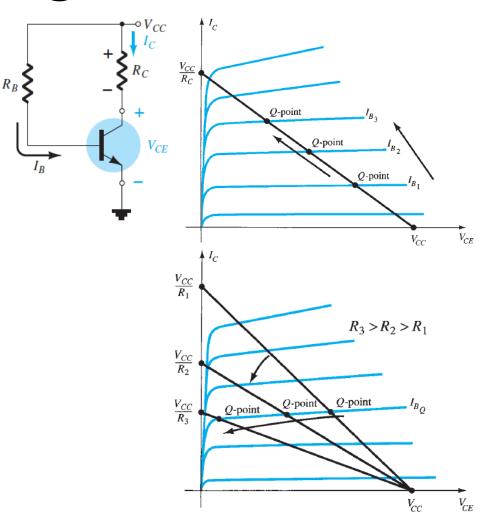




Load line analysis:

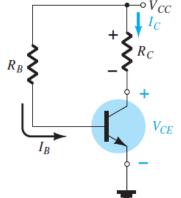
If I_B is changed by varying $R_B \rightarrow$

If V_{CC} is held fixed and R_C increased \rightarrow If I_B is held fixed \rightarrow



Load line analysis:

If R_C is fixed and V_{CC} decreased \rightarrow



Problem-23:

Given the load line of Fig. 23 and the defined Q-point, determine the required values of V_{CC} , R_C , and R_B for a fixed-bias configuration.

$$V_{CE}$$
 = V_{CC} = 20 V at I_C = 0 mA

$$I_C = V_{CC}/R_C$$
 at $V_{CE} = 0$ V $R_C = V_{CC}/I_C = 20/10 \times 10^{-3} = 2$ k Ω

$$I_B = (V_{CC} - V_{BE})/R_B$$

 $R_B = (V_{CC} - V_{BE})/I_B = (20 - 0.7)/25 \times 10^{-6} = 772 \text{ k}\Omega$

